WHAT IS CLAIMED IS:

1. A display device comprising:

plural groups including a light emitting element and a thin film transistor which is connected to the light emitting element;

wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.

2. A display device according to claim 1, the channel length of the first thin film transistor and the second thin film transistor is at least 5 times as long as a gate width, respectively.

3. A display device according to claim 1, the first thin film transistor and the second thin film transistor comprises a semiconductor layer which is formed by irradiating with a pulsed laser beam.

4. A display device comprising:

plural groups including a thin film transistor and a light emitting element in which brightness is fluctuated depending on an ON current value in a saturation region of a drain voltage-drain current characteristic of the thin film transistor;

wherein an absolute value of a fluctuation rate in an ON current value in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12 %.

5. A display device according to claim 2, the channel length of the first thin film transistor and the second thin film transistor is at least 5 times as long as a gate width, respectively.

6. A display device according to claim 2, the first thin film transistor and the second thin film transistor comprises a semiconductor layer which is formed by irradiating with a pulsed laser beam.

7. A display device comprising plural pixels including a driving thin film transistor, a switching thin film transistor, an erasing thin film transistor, a light emitting element which is connected to the driving thin film transistor;

wherein brightness is fluctuated depending on an ON current value in a saturation region of a drain voltage-drain current characteristic of the driving thin film transistor; and,

an absolute value of a fluctuation rate of the ON current value in a saturation region of the driving thin film transistor included in each a first pixel and a second pixel which is adjacent to the first pixel is at most 12%.

8. A display device according to claim 7, a channel length of the driving thin film transistor is at least 5 times as long as a gate width.

9. A display device according to claim 7, the driving thin film transistor comprises a semiconductor layer formed by irradiating with a pulsed laser beam.

10. An electronic device having the display device according to claim 1, wherein said electronic device is selected from the group consisting of a display device, a video camera, a notebook computer, a personal digital assistant, a digital still camera, and a mobile telephone.

11. An electronic device having the display device according to claim 4, wherein said electronic device is selected from the group consisting of a display device, a video camera, a notebook computer, a personal digital assistant, a digital still camera, and a mobile telephone.

12. An electronic device having the display device according to claim 7, wherein said electronic device is selected from the group consisting of a display device, a video camera, a

notebook computer, a personal digital assistant, a digital still camera, and a cellular phone.

13. A cellular phone comprising a main body, a display portion, a voice output portion, an operation switch, and an antenna;

said cellular phone comprising:

plural groups including a light emitting element and a thin film transistor which is connected to the light emitting element;

wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.

14. A notebook computer comprising a main body, a case, a display portion, and a keyboard;

said notebook computer comprising:

plural groups including a light emitting element and a thin film transistor which is connected to the light emitting element;

wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.

15. A semiconductor device comprising:

plural groups including a light emitting element and a thin film transistor which is connected to the light emitting element;

wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.

16. An electronic device having the semiconductor device according to claim 15, wherein said electronic device is selected from the group consisting of a display device, a video camera, a notebook computer, a personal digital assistant, a digital still camera, and a cellular phone.